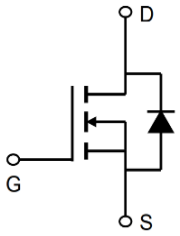
AP120N10NF

100V N-Channel Enhancement Mode MOSFET

Description

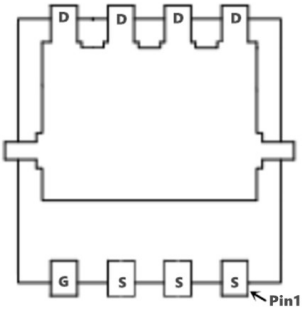
The AP120N10NF uses advanced SGTII technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.



General Features

V_{DS} = 100V I_D =120A

$R_{DS(ON)}$ < 4.5mΩ @ V_{GS}=10V **(Type：3.8mΩ)**

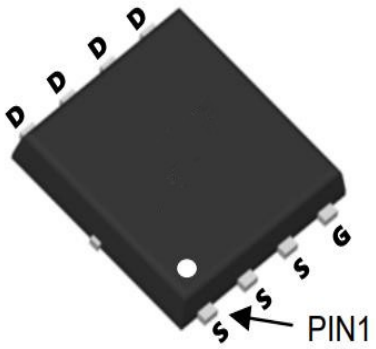


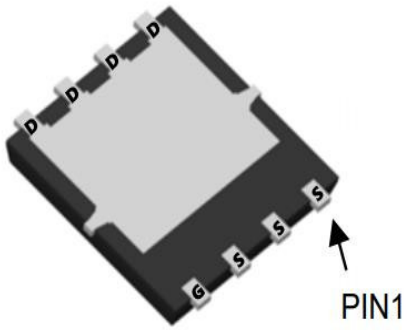
Application

Isolated DC

Motor control

Synchronous-rectification





Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
AP120N10NF	PDFN5*6-8L	AP120N10NF XXX YYYY	5000

Absolute Maximum Ratings (T_C=25℃unless otherwise noted)

Symbol	Parameter	Rating	Units
VDS	Drain-Source Voltage	100	V
VGS	Gate-Source Voltage	±20	V
I_D@T_A=25℃	Continuous Drain Current[1]	120	A
I_D@T_A=70℃	Continuous Drain Current[1]	76	A
IDM	Pulsed Drain Current[2]	480	A
EAS	Single Pulse Avalanche Energy[3]	320	mJ
IAS	Avalanche Current	40	A
P_D@T_A=25℃	Total Power Dissipation[4]	131.6	W
TSTG	Storage Temperature Range	-55 to 150	℃
T_J	Operating Junction Temperature Range	-55 to 150	℃
$R_{\theta}JA$	Thermal Resistance Junction-Ambient [1]	25	℃/W
$R_{\theta}JC$	Thermal Resistance Junction-Case[1]	0.95	℃/W

AP120N10NF

100V N-Channel Enhancement Mode MOSFET

Electrical Characteristics (T_C=25℃unless otherwise noted)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V(BR)DSS	Drain-Source Breakdown Voltage	V_{GS} = 0V, I_D = 250μA	100	107	-	V
IGSS	Gate-body Leakage current	V_{DS} = 0V, V_{GS} = ±20V	-	-	±100	nA
IDSS	Zero Gate Voltage Drain Current T_J=25°C	V_{DS} =100V, V_{GS} = 0V	-	-	1	μA
	Zero Gate Voltage Drain Current T_J=100°C		-	-	100	
VGS(th)	Gate-Threshold Voltage	V_{DS} = V_{GS}, I_D = 250μA	2.0	3.0	4.0	V
RDS(on)	Drain-Source on-Resistance[4]	V_{GS} = 10V, I_D = 20A	-	3.8	4.5	mΩ
gfs	Forward Transconductance[4]	V_{DS} = 10V, I_D = 20A	-	62	-	S
Ciss	Input Capacitance	V_{DS} = 50V, V_{GS} =0V, f =1MHz	-	6865	-	pF
Coss	Output Capacitance		-	740	-	
Crss	Reverse Transfer Capacitance		-	21	-	
R_g	Gate Resistance	f =1MHz	-	1.3	-	Ω
Q_g	Total Gate Charge	V_{GS} = 10V, V_{DS} = 50V, I_D=20A	-	111.2	-	nC
Qgs	Gate-Source Charge		-	30.5	-	
Qgd	Gate-Drain Charge		-	27.3	-	
td(on)	Turn-on Delay Time	V_{GS} =10V, V_{DD} =50V, R_G = 3Ω, I_D= 20A	-	33	-	ns
t_r	Rise Time		-	39	-	
td(off)	Turn-off Delay Time		-	67.1	-	
t_f	Fall Time		-	32	-	
trr	Body Diode Reverse Recovery Time	I_F = 20A, dI/dt=100A/μs	-	58.7	-	ns
Q_{rr}	Body Diode Reverse Recovery Charge		-	97.3	-	nC
VSD	Diode Forward Voltage[4]	I_S = 20A, V_{GS} = 0V	-	-	1.2	V
IS	Continuous Source Current T_C=25°C	-	-	-	120	A

Note :

1、The data tested by surface mounted on a 1 inch 2 FR-4 board with 2OZ copper.

2、The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%

3、The EAS data shows Max. rating . The test condition is VDD=72V,VGS=10V, L=0.1mH IAS=40A

4、The power dissipation is limited by 150℃ junction temperature

5、The data is theoretically the same as I D and I DM , in real applications , should be limited by total power dissipation

Typical Characteristics

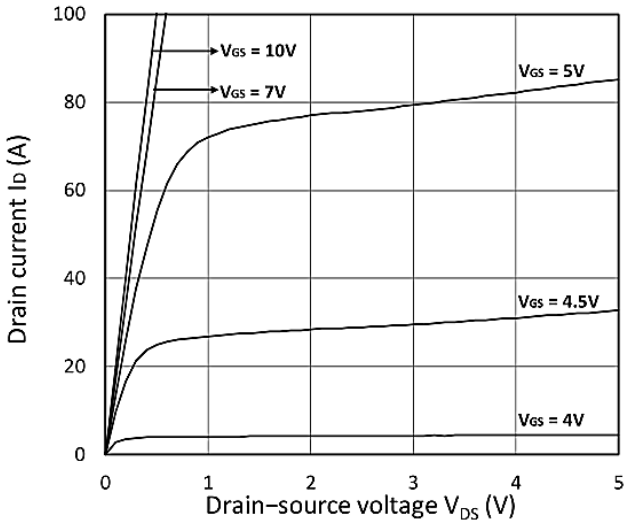


Figure 1. Output Characteristics

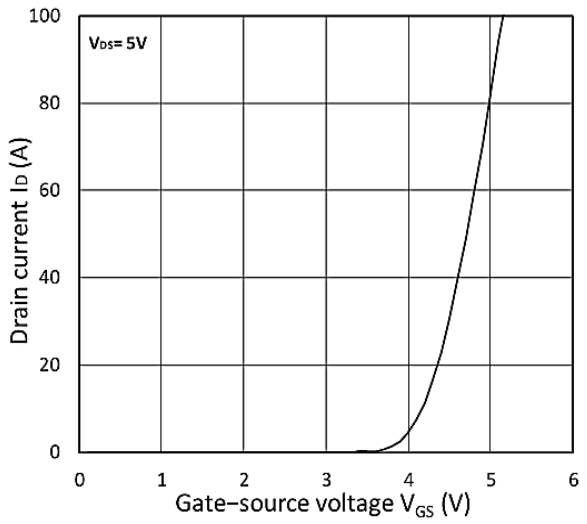


Figure 2. Transfer Characteristics

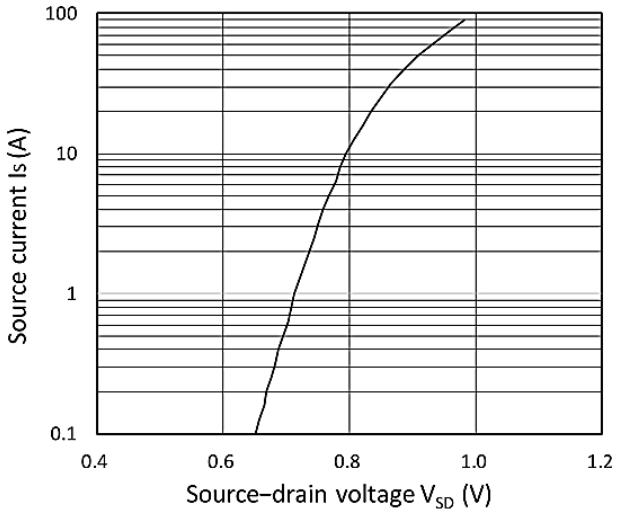


Figure 3. Forward Characteristics of Reverse

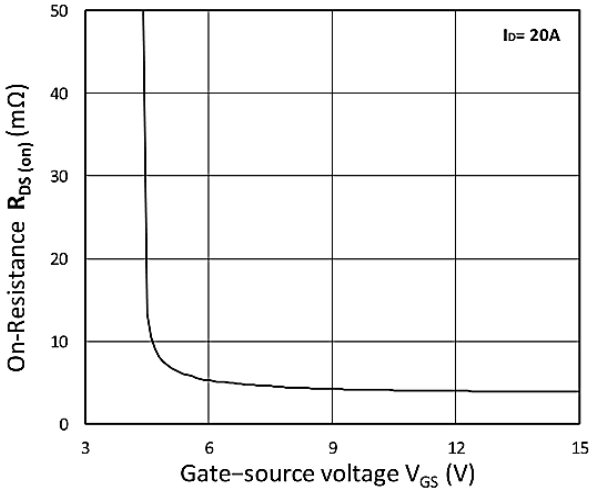


Figure 4. RDS(ON) vs. VGS

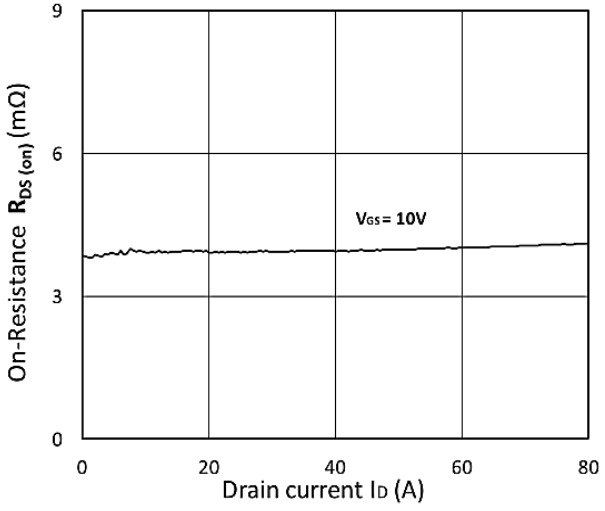


Figure 5. RDS(ON) vs. ID

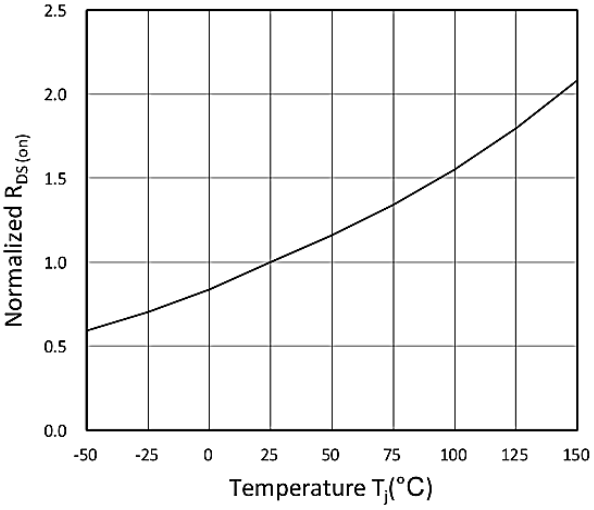


Figure 6. Normalized RDS(on) vs. Temperature

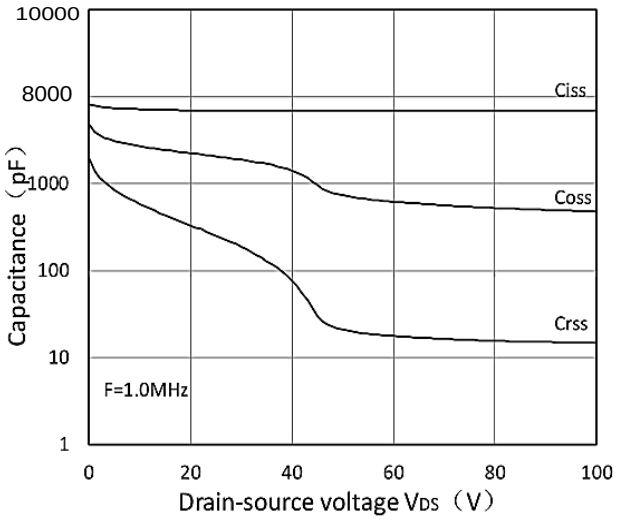


Figure 7. Capacitance Characteristics

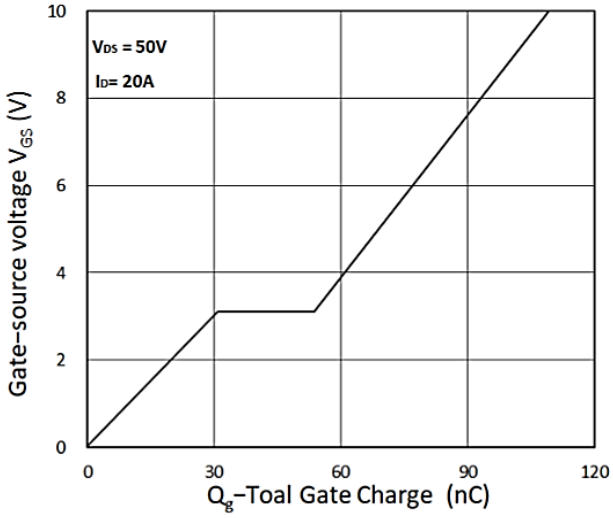


Figure 8. Gate Charge Characteristics

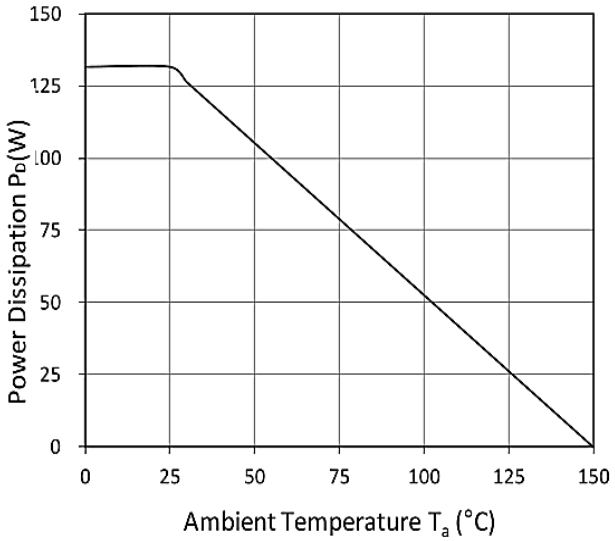


Figure 9. Power Dissipation

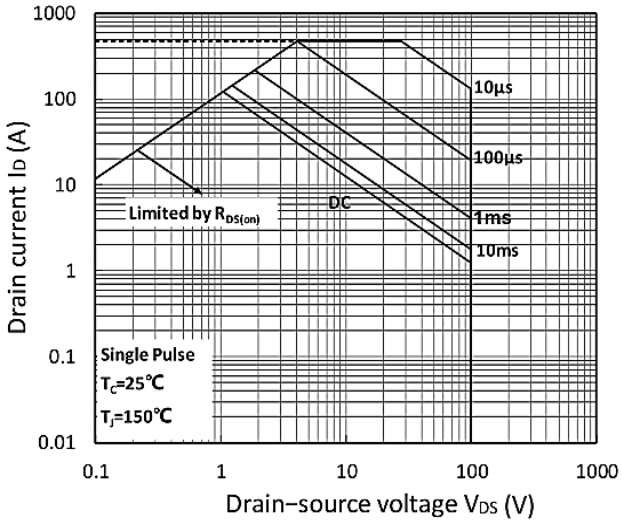


Figure10. Safe Operating Area

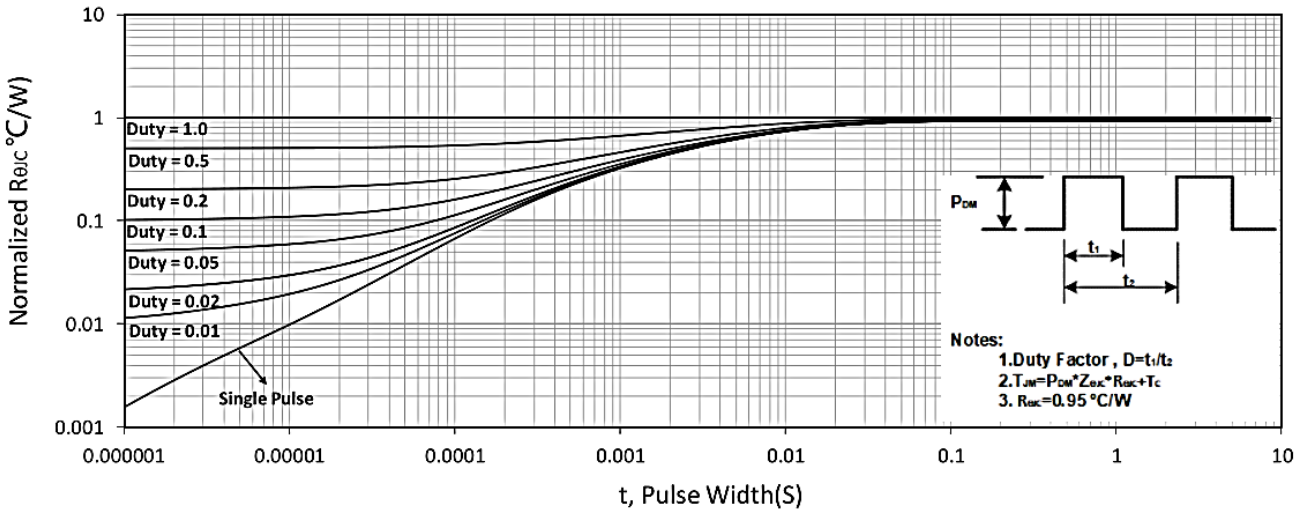
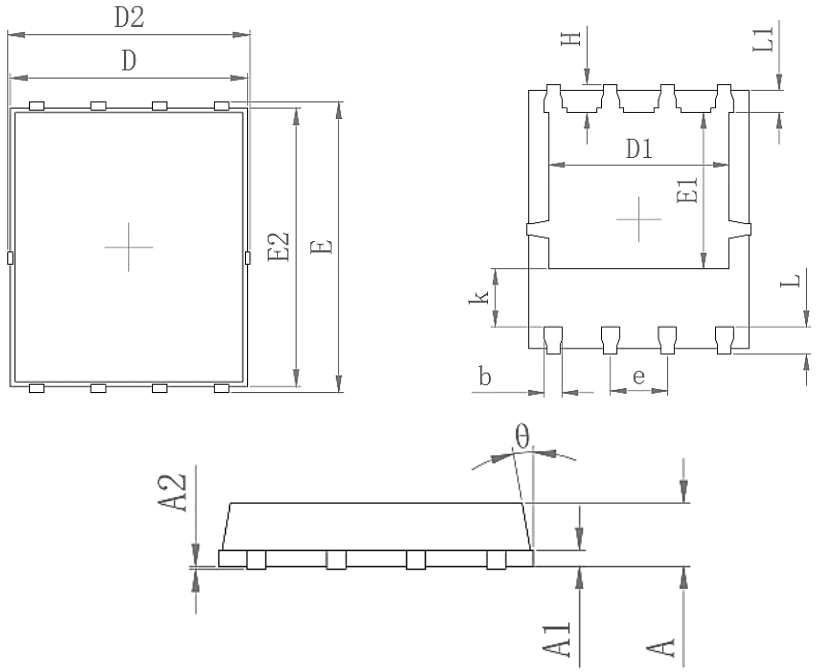


Figure 11. Normalized Maximum Transient Thermal Impedance

Package Mechanical Data-PDFN5X6-8L-XZT Single



Symbol	Common	
	mm	
	Mim	Max
A	0.90	1.10
A1	0.254 REF	
A2	0-0.05	
D	4.824	4.976
D1	3.910	4.110
D2	4.944	5.076
E	5.924	6.076
E1	3.375	3.575
E2	5.674	5.826
b	0.350	0.450
e	1.270	
L	0.534	0.686
L1	0.424	0.576
K	1.190	1.390
H	0.549	0.701
Φ	8°	12°